

IGBT Modules

Power Module (V series) 1200V / 200A / 2-in-1 package

■ Features

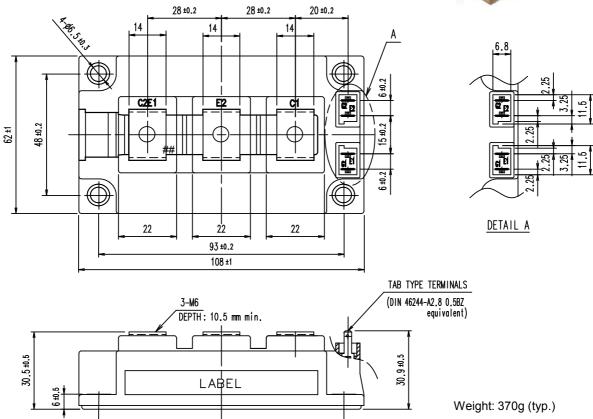
High speed switching Voltage drive Low Inductance module structure

■ Applications

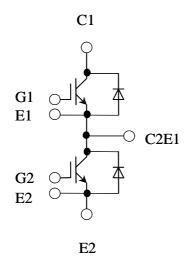
Soft-switching Application Industrial machines, such as Welding machines

■ Outline drawing (Unit:mm)





■ Equivalent Circuit



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■ Absolute Maximum Ratings (at T_C= 25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum Ratings	Units
Collector-	Emitter voltage	V _{CES}			1200	V
Gate-Emit	ter voltage	V_{GES}			±20	V
		1	Continuous	T _C =60°C	200	
		I _C	Continuous	T _C =25°C	275	1
Collector	current	I _C pulse	1ms		400	Α
		-I _C			300	
		-I _C pulse	1ms		600	
Collector power dissipation		Pc	1 device		1385	W
Junction temperature		T _j			150	
Case temperature		T _C			125	°C
Storage temperature		T _{stg}			-40 ~ 125	
Isolation	between terminal and copper base	V _{iso}	AC: 1min.		2500	VAC
voltage	(*1)	- 180	7.0		2300	., 10
Screw	Mounting (*2)	-			6.0	N m
Torque	Terminals (*3)	-			5.0	INIII

(*1) All terminals should be connected together during the test.

(*2) Recommendable Value: 3.0-6.0 Nm (M5 or M6)

(*3) Recommendable Value: 2.5-5.0 Nm (M6)

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■ Electrical characteristics (at T_j= 25°C unless otherwise specified)

Items Symbols		Condition		Ch	aracterist	eristics	
items	Syllibols	Conditions		min.	typ.	max.	Units
Zero gate voltage Collector current	I _{CES}	VGE=0V, VCE=1200V		-	-	4.0	mA
Gate-Emitter leakage current	I _{GES}	VCE=0V, VGE=±20V	/	-	-	800	nA
Gate-Emitter threshold voltage	$V_{GE(th)}$	VCE=20V, Ic=200mA	4	5.7	6.2	6.7	٧
	$V_{CE(sat)}$	VGE=15V, Ic=200A	T _i =25°C		3.60	3.90	
Collector-Emitter	(terminal)	VGE=15V, IC=200A	T _i =125°C	-	4.50	_	V
saturation voltage	V _{CE(sat)}	VOE 45V I- 000A	T _i =25°C	-	3.20	3.50	_ v
	(chip)	VGE=15V, Ic=200A	T _i =125°C	-	4.10	-	1
miemai gale resistance	R _{G(int)}	-		-	0.8	-	Ω
Input capacitance	C _{ies}	V _{CE} =10V, V _{GE} =0V, f:	=1MHz	-	15.2	-	nF
	t _{on}			-	250	-	
Turn-on time	t _r	Vcc= 600V I _C =	200A	-	180	-	
	t _{r(i)}	V_{GE} = ±15V R_{G} =	4.7Ω	-	40	-	nsec
Turn off times	t _{off}	T _i = 125°C L _s =	30nH	-	300	-	
Turn-off time	tf			-	50	-	1
	V _F	\/CE=0\/.IE=200A	T _i =25°C	-	2.15	2.40	
Camusad on voltors	(terminal)	VGE=0V,IF=300A	T _i =125°C	-	2.30	-	.,
Forward on voltage	V _F	VOE 01/15 0003	T _i =25°C	-	1.70	1.95	V
	(chip)	VGE=0V,IF=300A	T _i =125°C	-	1.85	-	1
Reverse recovery time	t _{rr}	IF=200A		-	130	-	nsec

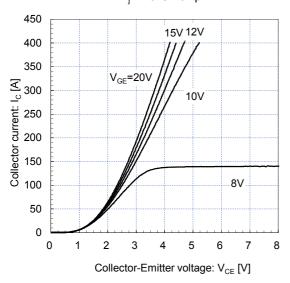
5. Thermal resistance characteristics

Items	Symbols	Conditions	Ch	Characteristics		Units
	Syllibols	Conditions	min.	typ.	max.	Ullita
Thermal resistance	D	IGBT	-	-	0.090	
(1device)	$R_{th(j-c)}$	FWD	-	-	0.140	°C/W
Contact thermal resistance (1device) (*1)	R _{th(c-f)}	with thermal compound	-	0.0125	-	C/VV

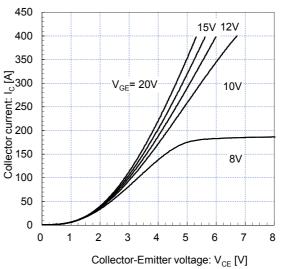
^(*1) This is the value which is defined mounting on the additional cooling fin with thermal compound.

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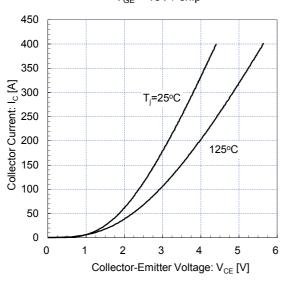
Collector current vs. Collector-Emitter voltage $T_i = 25^{\circ}C$ / chip



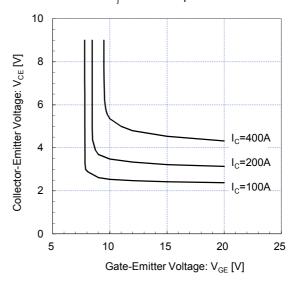
Collector current vs. Collector-Emitter voltage (typ.) $T_j = 125^{\circ}C$ / chip



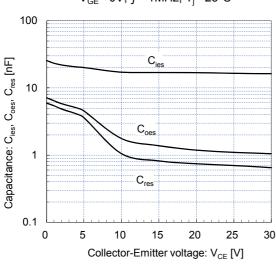
Collector current vs. Collector-Emitter voltage $V_{GE} = 15V / chip$



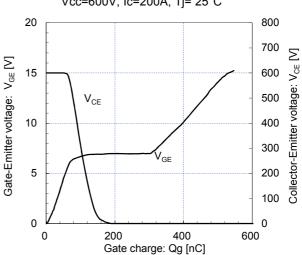
Collector-Emitter voltage vs. Gate-Emitter voltage $T_i = 25^{\circ}\text{C}$ / chip



Capacitance vs. Collector-Emitter Voltage V_{GE} = 0V, f= 1MHz, T_i = 25°C

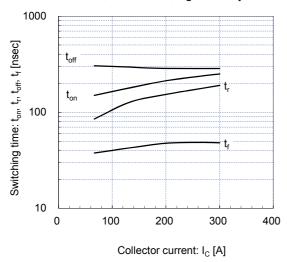


Dynamic Gate Charge (typ.) Vcc=600V, Ic=200A, Tj= 25°C

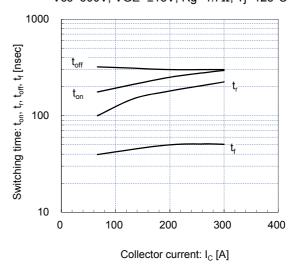


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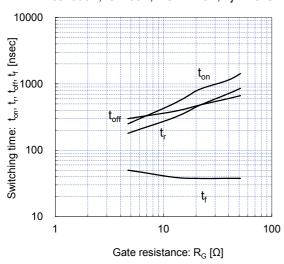
Switching time vs. Collector current (typ.) Vcc=600V, $VGE=\pm15V$, $Rg=4.7\Omega$, $Tj=25^{\circ}C$



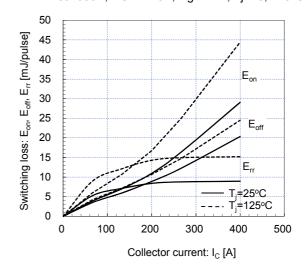
Switching time vs. Collector current (typ.) Vcc=600V, VGE=±15V, Rg=4.7Ω, Tj=125°C



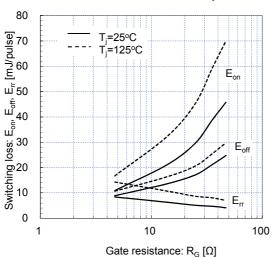
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=200A, VGE=±15V, Tj=125°C



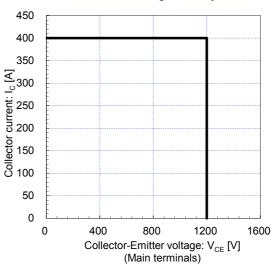
Switching loss vs. Collector current (typ.) Vcc=600V, VGE=±15V, Rg=4.7Ω, Tj=25, 125°C



Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=200A, VGE=±15V, Tj=25, 125°C



Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, Rg= 4.7Ω , Tj= 125° C





0.0

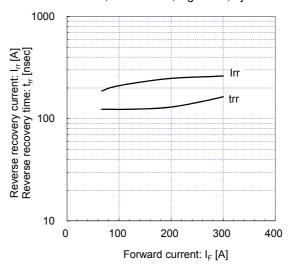
2MBI200HJ-120-50

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700 T_i=25°C 600 Forward current: I_F [A] 000 000 000 125°C 100 0 0.5 1.0 1.5

Forward current vs. Forward vltage (typ.)

Reverse recovery characteristics (typ.) Vcc=600V, VGE=±15V, Rg=4.7Ω, Tj=125°C



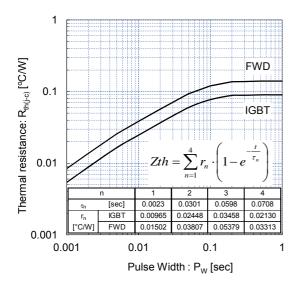
Transient thermal resistance (max.)

Forward on voltage: V_F [V]

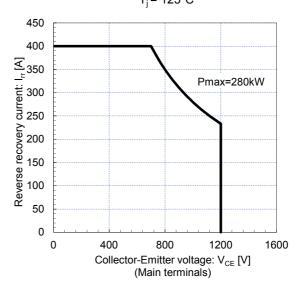
2.0

2.5

3.0



FWD safe operating area (max.) T_j = 125°C



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